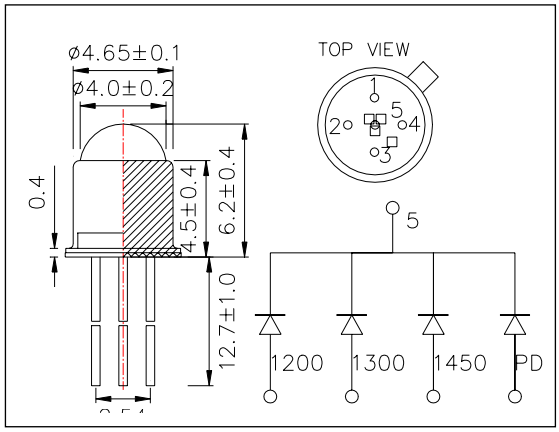
L1200/1300/1450/PD-35B32

Multi-Wavelength LED

This product consists of InGaAs LEDs and an InGaAs PD mounted on TO-18 stem with a spherical glass lens. And it is designed to monitor reflected light through detector for controlling its own output power.

Outer Dimension (Unit:mm)



<Specifications>

1. Product Name: Multi-Wavelength LED Lamp
2. Type Number: L1200/1300/1450/PD-35B32
3. Chip:
   - Chip material: InGaAs(LED/PD)
   - Peak Wavelength: 1200,1300,1450nm
4. Package:
   - Stem: TO-18, 5pins type
   - Lens: Φ5mm Spherical Glass

Absolute Maximum Ratings/per each one chip[Ta=25℃]

Device	Item	Symbol	Maximum Rated Value	Unit
LED	Power Dissipation	PD	120	mW
LED	Forward Current	IF	100	mA
LED	Pulse Forward Current	IFP	1000	mA
LED	Reverse Voltage	VR	5	V
PD	Reverse Voltage	VR	10	V
	Operating Temperature	TOPR	-20 ~ +80	℃
	Storage Temperature	TSTG	-30 ~ +100	℃
	Soldering Temperature*	TSOL	240	℃

* Soldering condition must be completed within 3 seconds at 240℃
and it is allowed in the area apart 3mm from the bottom of the lamp.

Electro-Optical Characteristics/per each one chip [Ta=25℃]

Device	Item	Symbol	Condition	Minimum			Typical			Maximum			Unit
				1200	1300	1450	1200	1300	1450	1200	1300	1450	
LED	Forward Voltage	VF	IF=20mA				0.8	0.8	0.8	1.3	1.3	1.3	V
	Reverse Current	IR	VR=5V								10		uA
	T. Radiated Power*	PO	IF=20mA				1.3	1.3	1.0				mW
	Peak Wavelength	λP	IF=20mA	1150	1250	1400	1200	1300	1450	1250	1350	1500	nm
	Half Width	Δλ	IF=20mA				75	75	75				nm
PD	Output Current	IL	IF=20mA VR=0V				45	45	35				uA
	Dark Current	ID	VR=10V								100		nA

* Measured by Photodyne #500
(Radiated Power of NIR LED is measured by Ando Optical Multi Meter AQ2140&AQ2742)

RoHS Compliant

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